

	Hits	Search Text	DBs
1	56	porous adj silicon same dielectric adj constant	USPAT
2	1	gate adj insulator same porous and 445/24	USPAT
3	3	gate adj insulator same porous and 313/309	USPAT
4	105	micron and oxidiz\$ same porous adj silicon	USPAT
5	6	445/24 and oxidiz\$ same porous adj silicon not (micron and oxidiz\$ same porous adj silicon)	USPAT
6	15	(US-5834845-\$ or US-5527737-\$ or US-6232705-\$ or US-5529524-\$ or US-5981303-\$ or US-5898258-\$ or US-5458518-\$ or US-6333215-\$ or US-6309956-\$ or US-6277765-\$ or US-6255156-\$ or US-6251470-\$ or US-6163066-\$ or US-6156374-\$ or US-6072227-\$).did.	USPAT
7	15	(US-5834845-\$ or US-5527737-\$ or US-6232705-\$ or US-5529524-\$ or US-5981303-\$ or US-5898258-\$ or US-5458518-\$ or US-6333215-\$ or US-6309956-\$ or US-6277765-\$ or US-6255156-\$ or US-6251470-\$ or US-6163066-\$ or US-6156374-\$ or US-6072227-\$).did.	USPAT
8	5	rrrrrrrr	USPAT
9	7	((US-5834845-\$ or US-5527737-\$ or US-6232705-\$ or US-5529524-\$ or US-5981303-\$ or US-5898258-\$ or US-5458518-\$ or US-6333215-\$ or US-6309956-\$ or US-6277765-\$ or US-6255156-\$ or US-6251470-\$ or US-6163066-\$ or US-6156374-\$ or US-6072227-\$).did.) and anodiz\$	USPAT
10	1	((US-5834845-\$ or US-5527737-\$ or US-6232705-\$ or US-5529524-\$ or US-5981303-\$ or US-5898258-\$ or US-5458518-\$ or US-6333215-\$ or US-6309956-\$ or US-6277765-\$ or US-6255156-\$ or US-6251470-\$ or US-6163066-\$ or US-6156374-\$ or US-6072227-\$).did.) and thermal\$ adj oxidiz\$	USPAT

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11	0	(US-5834845-\$ or US-5527737-\$ or US-6232705-\$ or US-5529524-\$ or US-5981303-\$ or US-5898258-\$ or US-5458518-\$ or US-6333215-\$ or US-6309956-\$ or US-6277765-\$ or US-6255156-\$ or US-6251470-\$ or US-6163066-\$ or US-6156374-\$ or US-6072227-\$).did. and (void or cavity) same percent same anodiz\$	USPAT
12	9	(void or cavity) same percent and silicon with anodiz\$	USPAT
13	9	(void or cavity) same percent and silicon with anodiz\$	USPAT
14	0	volumn same percent and silicon with anodiz\$	USPAT
15	0	volumn same percent same silicon near4 porous	USPAT
16	0	volumn same percent and silicon near4 porous	USPAT
17	87	percent same "75" and silicon near4 porous	USPAT
18	91	silicon same anodiz\$ same porosity	USPAT
19	1	silicon same anodiz\$ same column\$ near3 structure	USPAT
20	0	silicon same anodiz\$ same column\$ near3 microstructure	USPAT
21	26	silicon same anodiz\$ same microstructure	USPAT
22	5	silicon near3 porous and dielectric near4 1.6	USPAT
23	33	445/24 and low adj dielectric	USPAT
24	2	2593953.pn.	DERWENT
25	0	field adj emitters same silicon adj monoxide	USPAT
26	4	field adj emitters and silicon adj monoxide	USPAT
27	1	(field adj emitters and silicon adj monoxide) and porous same oxidiz\$	USPAT
28	3	(field adj emitters and silicon adj monoxide) not ((field adj emitters and silicon adj monoxide) and porous same oxidiz\$)	USPAT